AOE 3.1 Design a 1 mA current sink using the 2N5484 JFET.

Use the circuit layout shown in Fig 3.23.

Vod
$$V_{GS} = -I_{D}R$$

We want $I_{D} = I_{M}A$.

Tov Load From Fig. 3.21 A, this means $V_{GS} \approx -0.6 \text{ V}$.

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 $V_{GS} \approx -0.001 R$
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However: JFET manufacturing variability would be a problem here. IDSS ranges from 1 mA to 5 mA. This would create a lot of variation in ID (see Fig 3.25).